

Data Sheet

May 27, 2010

FN3401.5

Radiation Hardened Quad Differential Line Driver

intercil

The Intersil HS-26C31RH is a quad differential line driver designed for digital data transmission over balanced lines and meets the requirements of EIA standard RS-422. Radiation hardened CMOS processing assures low power consumption, high speed, and reliable operation in the most severe radiation environments.

The HS-26C31RH accepts CMOS signal levels and converts them to RS-422 compatible outputs. This circuit uses special outputs that enable the drivers to power-down without loading down the bus. Enable and disable pins allow several devices to be connected to the same data source and addressed independently.

Specifications

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

Detailed Electrical Specifications for these devices are contained in SMD 5962-96663. A "hot-link" is provided on our homepage for downloading. www.intersil.com/military/

Features

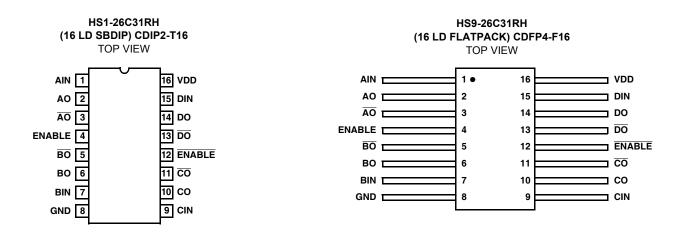
- · Electrically Screened to SMD # 5962-96663
- QML Qualified per MIL-PRF-38535 Requirements
- 1.2 Micron Radiation Hardened CMOS
 - Total Dose Up to 300kRAD(Si)
- Latchup Free
- EIA RS-422 Compatible Outputs (Except for IOS)
- CMOS Inputs
- High Impedance Outputs when Disabled or Powered Down
- Low Power Dissipation 2.75mW Standby (Max)
- Single 5V Supply
- Full -55°C to +125°C Military Temperature Range

Applications

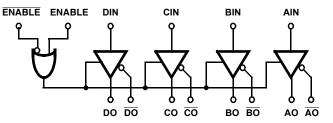
· Line Transmitter for MIL-STD-1553 Serial Data Bus

| ORDERING NUMBER | INTERNAL MKT. NUMBER | PART MARKING | TEMP. RANGE (°C) | PACKAGE | PKG. DWG. # |
|--------------------|-------------------------|--------------------|---------------------|----------------|----------------|
| 5962F9666301QEC | HS1-26C31RH-8 | Q 5962F96 6630QEC | -55 to +125 | 16 LD SBDIP | D16.3 |
| 5962F9666301QXC | HS9-26C31RH-8 | Q 5962F96 66301QXC | -55 to +125 | 16 LD FLATPACK | K16.A |
| 5962F9666301VEC | HS1-26C31RH-Q | Q 5962F96 66301VEC | -55 to +125 | 16 LD SBDIP | D16.3 |
| 5962F9666301VXC | HS9-26C31RH-Q | Q 5962F96 66301VXC | -55 to +125 | 16 LD FLATPACK | K16.A |
| HS1-26C31RH/PROTO | HS1-26C31RH/PROTO | HS1-26C31RH/PROTO | -55 to +125 | 16 LD SBDIP | D16.3 |
| HS9-26C31RH/PROTO | HS9-26C31RH/PROTO | HS9-26C31RH/PROTO | -55 to +125 | 16 LD FLATPACK | K16.A |
| 5962F9666301V9A | HSO-26C31RH-Q | | -55 to +125 | | |

Pinouts



Logic Diagram



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Die Characteristics

DIE DIMENSIONS:

96.5 mils x 195 mils x 21 mils (2450 x 4950)

INTERFACE MATERIALS:

Glassivation:

Type: PSG (Phosphorus Silicon Glass) Thickness: 10kÅ ±1kÅ

Metallization:

M1: Mo/TiW Thickness: 5800Å M2: Al/Si/Cu (Top) Thickness: 10kÅ ±1kÅ

Metallization Mask Layout

Substrate:

AVLSI1RA

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION: Substrate Potential (Powered Up): V_{DD}

ADDITIONAL INFORMATION: Worst Case Current Density:

<2.0x10⁵A/cm²

Bond Pad Size:

110µmx100µm

